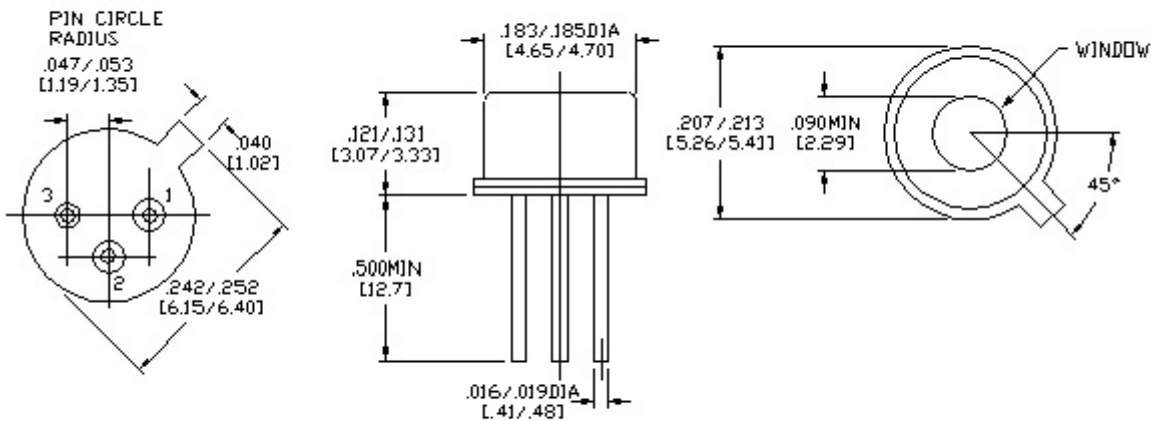


**DESCRIPTION**

This is a high speed Silicon detector optimized for applications requiring high Responsivity and a fast response time.

**FEATURES**

- High Responsivity
- High Electrical
- High Reliability/Hermetic Package



**ABSOLUTE MAXIMUM RATINGS**

- Storage temperature..... -65°C to +150°C
- Case operating temperature..... -55°C to +125°C
- Lead solder temperature..... 260°C, 10 seconds
- Reverse Breakdown Voltage..... 100 Volts

**OUTLINE DIMENSIONS**

Tolerances are +/-0.005 inches, except as noted  
The case is electrically isolated from the pins.  
Pin 1. Anode, Pin 2. Cathode, Pin 3. Cathode (Case)

| PARAMETER                               | TEST CONDITION   | SYMBOL         | MIN | TYP        | MAX      | UNIT         |
|---|--|----------------|-----|------------|----------|--------------|
| Capacitance                             | $V_r = 20 \text{ V}, f = 1 \text{ MHz}$ C  |                | 3.0 |            |          | pF           |
| Responsivity (50 $\mu\text{m}$ coupled) | $H = 10 \mu\text{W}, V_r = 5 \text{ Volts}$<br>50 $\mu\text{m}$ Core, $\lambda = 850 \text{ nm}$ | $R_c$          | .45 | .55        |          | A/W          |
| Dark Current                            | $V_r = 5 \text{ Volts}, H = 0 \text{ mW}$  | $I_d$          |     | 2          | 10       | nA           |
| Response Time                           | 10%-90%, $V_r = 5 \text{ Volts}$<br>$R_L = 50 \Omega$  | $t_r$<br>$t_f$ |     | 6.0<br>6.0 | 10<br>10 | nsec<br>nsec |
| Spectral Response                       |  | $\lambda$      | 400 |            | 1100     | nm           |
| Electrical Bandwidth                    | $V_r = 5 \text{ Volts}$  | BWE            |     | 50         |          | MHz          |

**ELECTRO-OPTICAL CHARACTERISTICS (Case T = 25°C)**

distributed by



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